GaN Power Amp Pallet SMPA3135-750V

Product Features

3.1-3.5GHz:>750W, pulsed CW

>50% Drain Efficiency@50V

50ohm in and out, screw down

Device used: STBV35700BY2

Applications

5G Power amplifier

S band communication

ISM

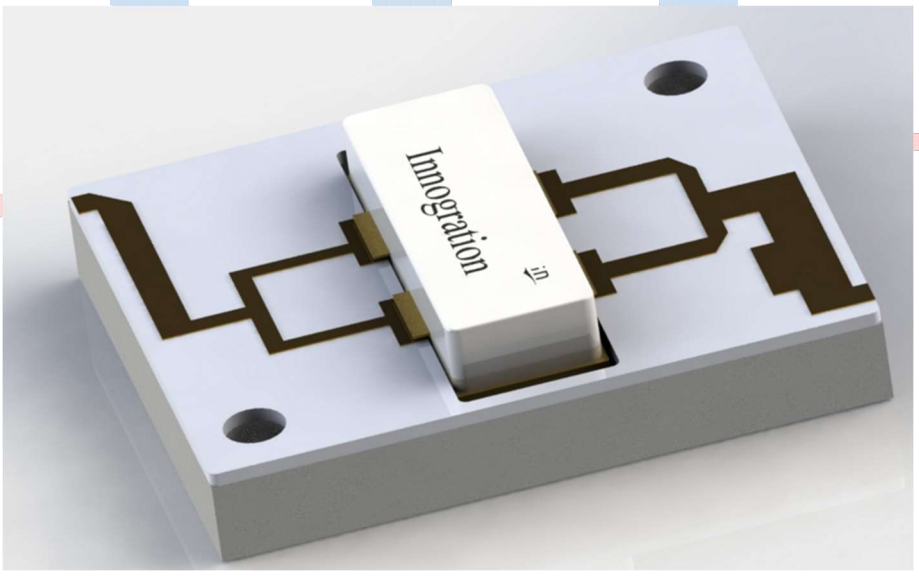
Commercial pulsed CW Power amplifier

Description

The SMPA3135-750V is designed for 5G communication, test and measurement and other ISM applications at 3100-3500MHz. This Amplifier pallet is suitable for use in linear and saturated applications. Featured by 50ohm fully matched at input and output, drop-in placement by screwing it down and 100% RF test, it enables easier power combination to reach higher power with high production yield as part of customer's power amplifier system.

This standard pallet is with typical size 50*90mm, but can be shrunk to much smaller size.

Pallet concept demostration purpose only, Not exactly the design itself



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Electrical Specifications @VCC=50V, T=25℃, 50Ωsystem

PARAMETER	UNIT	MIN	TYP	MAX	SYMBOL
Operating Frequency	MHz	3100	-	3500	fo
Operating Bandwidth	MHz	400		-	OBW
Pulse CW Output Saturated Power	W	750		-	Psat
Power Gain	dB	9	10	-	G_P
Gain Flatness	dB	-	-	±0.5	G_F
Input Return Loss	dB	-	-	-10	S_{11}
Operating Voltage	V	-	50	55	V_{DS}
Quiescent Current	mA	-	100	-	I_{DQ}
Efficiency@Psat	%	50		-	Eff

Environmental Characteristics

PARAMETER	UNIT	MIN	TYP	MAX	SYMBOL
Operating Case Temperature	℃	-40	-	60	Ta
Storage Temperature	℃	-40		100	Tstg
Relative humidity w/o condensation	%	-	-	95	RH

Mechanical Specifications

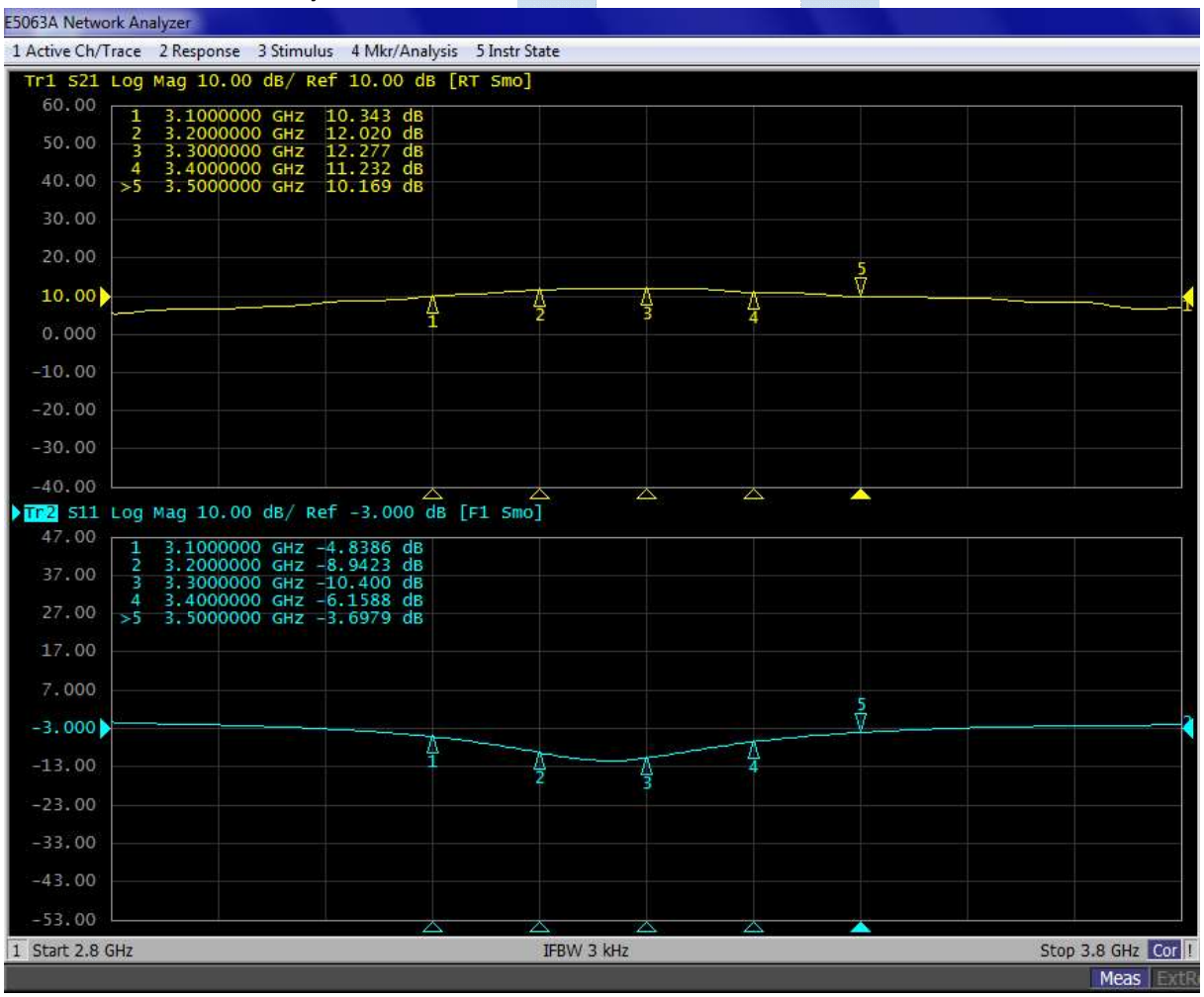
PARAMETER	UNIT	VALUE
Dimensions(L × W × H)	mm	50×90×4
RF Input Connector	-	N/A
RF Output Connector	-	N/A
Cooling	-	External Heat-sink

Typical performance

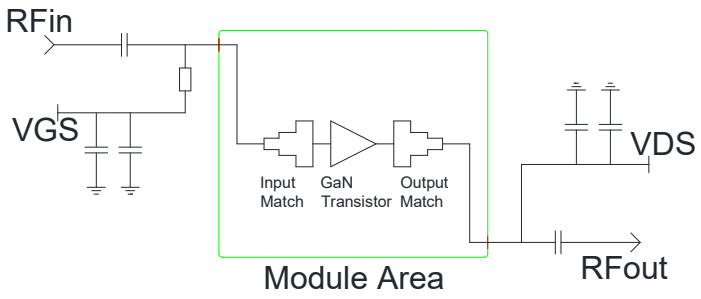
- **Pulsed CW performance:**

STBV35700BY2 v0 Vds=50V,Vgs=-3.46V,Idq=110mA Pulse:60us,20%						
Freq(MHz)	**Pin(dBm)**	**Psat(dBm)**	**Psat(W)**	**Ids(A)**	**Gain(dB)**	**Eff(%)**
3100	50.87	59.81	957.2	7.78	8.9	50.1
3200	49.90	59.90	977.2	7.45	10.0	52.5
3300	48.77	59.64	920.4	6.87	10.9	53.6
3400	49.24	59.62	916.2	7.04	10.4	52.1
3500	50.12	59.48	887.2	6.64	9.4	53.4

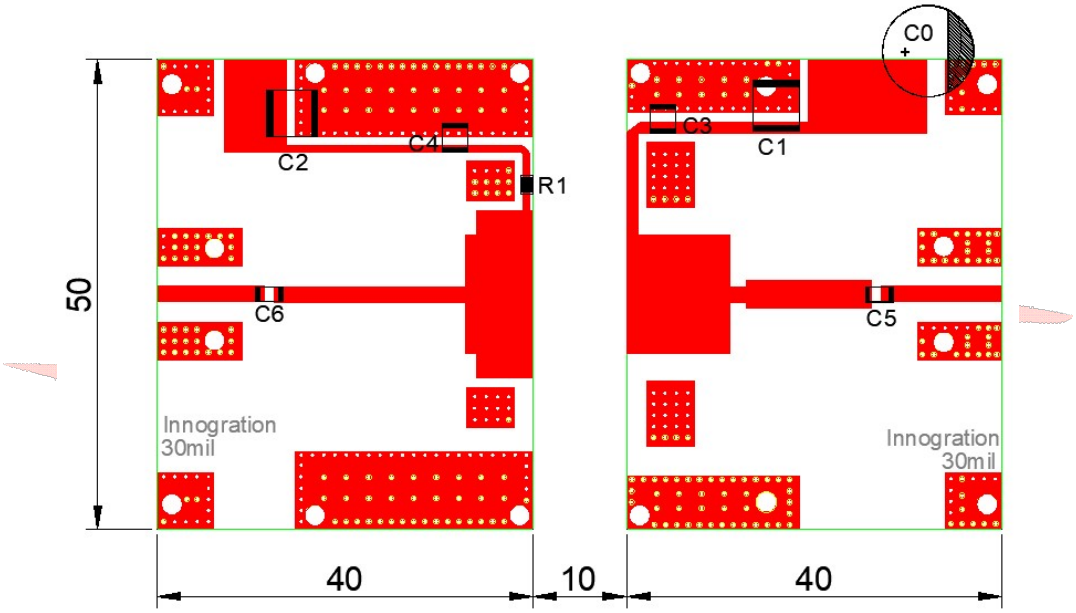
- **S21/S11 from network analyzer VDS=50V VGS=-3.02V IDQ=500mA**



Evaluation board Block Diagram



Evaluation board outline (DUT:STBV35700BY2)



Component	Description	Suggestion
C0	470uF/63V	
C1, C2	10uF	5750
C3, C4, C5, C6	10pF	MQ301111
R1	Chip Resistor, 10Ω	0805
PCB	30 Mil Rogers 4350B	

Revision History

Document revision history

Date	Revision	Datasheet Status
2023/7/2	Rev 1.0	Preliminary Datasheet

Application data based on RXT-23-26

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